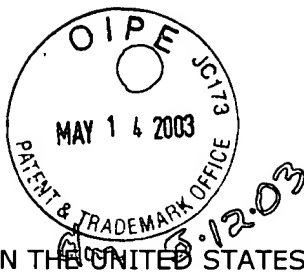


MTS-2700US1



PATENT

5.2003
C. Moore

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yuji Judai : Art Unit: 2814
Serial No.: November 21, 2001 : Examiner: H. Weiss
Filed: 09/990,474 :
FOR: A METHOD FOR FORMING A :
SEMICONDUCTOR DEVICE (AS AMENDED) :

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

S I R :

Responsive to the Official Action dated **January 10, 2003**, please amend the
above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 8 and 9.

Please amend the claims to read as indicated:

C1
5. (Twice Amended) The method for forming a semiconductor device
according to claim 16, in which said step f1) comprises:
depositing said second insulating film using a TEOS-CVD method utilizing TEOS
activated by O₃.

C2
11. (Twice Amended) The method for forming a semiconductor device
according to claim 16, wherein said upper layer is an Al layer.

12. (Twice Amended) The method for forming a semiconductor device
according to claim 11, wherein

said step of depositing said Al layer comprises sputtering while heating said circuit
board in a temperature range of 100 to 400°C.

C3
16. (Amended) A method for forming a semiconductor device, comprising the
steps of: